

Application No. 09/855,493  
Reply to Office Action of May 14, 2003

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

Claims 1-21 (Canceled)

Claim 22 (Currently Amended): The apparatus according to Claim ~~24~~ 49, wherein the conductive film comprises at least one of silicon carbide and titanium oxide.

Claim 23 (Currently Amended): The apparatus according to Claim ~~24~~ 49, wherein the conductive film is a film formed by means of chemical vapor deposition.

Claim 24 (Currently Amended): The apparatus according to Claim ~~24~~ 49, wherein the conductive film is a film formed by means of thermal spraying.

Claim 25 (Currently Amended): The apparatus according to Claim ~~24~~ 49, wherein the conductive film has a thickness ranging from 20 to 100  $\mu\text{m}$ .

Claim 26 (Currently Amended): The apparatus according to Claim ~~24~~ 49, wherein the worktable and the pedestal comprise insulating surfaces on which the conductive film is formed.

Claim 27 (Currently Amended): The apparatus according to Claim 26, wherein portions of the worktable and the pedestal facing an atmosphere in the process chamber are covered with the conductive film.

Claim 28 (Currently Amended): The apparatus according to Claim 49, wherein ~~the conduction structure is arranged such that~~ the conductive film ~~and~~ is electrically connected to

a conductive portion of ~~the~~ a casing of the process chamber, which is grounded ~~are~~  
~~electrically connected to ground.~~

Claim 29 (Currently Amended): The apparatus according to Claim 49, wherein the pedestal is attached to the process chamber by a fixing member which penetrates a casing of the process chamber, and ~~the conduction structure is arranged such that~~ a conductive portion of the fixing member is electrically connected to the conductive film.

Claim 30 (Previously Presented): The apparatus according to Claim 29, further comprising:

a bias section configured to selectively apply a positive electrical potential to the conductive portion of the fixing member.

Claim 31 (Previously Presented): The apparatus according to Claim 30, wherein the bias section comprises:

a switch configured to switch between a state where the conductive portion of the fixing member is grounded and a state where the conductive portion of the fixing member is connected to the bias section.

Claim 32 (Currently Amended): The apparatus according to Claim ~~24~~ 49, further comprising:

a supply section configured to supply a process gas into the process chamber;

an exhaust section configured to vacuum-exhaust the process chamber,

a window formed in a ~~the~~ casing of the process chamber and facing the worktable;

and

a UV lamp disposed outside the process chamber and facing the window, the UV lamp being configured to radiate UV rays onto the process gas above the worktable to activate the process gas.

Claim 33 (Previously Presented): The apparatus according to Claim 32, wherein the process gas contains an oxidizing gas for subjecting the target substrate to oxidation.

Claim 34 (Previously Presented): The apparatus according to Claim 33, wherein the oxidizing gas comprises ozone gas.

Claims 35-48 (Canceled)

Claim 49 (New): A single-substrate-processing apparatus for performing a semiconductor process, comprising:

an airtight process chamber configured to process a target substrate;

a ceramic heater disposed within the process chamber, and having a worktable configured to support and heat the target substrate, and an insulating pedestal connected to the worktable to support the worktable; and

a conductive film formed on a surface of the ceramic heater and on a surface of the insulating pedestal, and electrically connected at a lower end of the pedestal to a grounded portion, which is disposed as a part of the process chamber or disposed outside the process chamber.

Claim 50 (New): The apparatus according to claim 49, wherein the pedestal is attached to a casing of the process chamber by a flange and a fixing member, and stands within the process chamber.

Claim 51 (New): The apparatus according to claim 50, wherein the conductive film is electrically connected to a conductive portion of the flange and a conductive portion of the fixing member, and is electrically connected to the grounded portion disposed outside the process chamber through the conductive portion of the fixing member.

Claim 52 (New): The apparatus according to claim 51, wherein the conductive portions of the flange and the fixing member are electrically isolated from the casing.

Claim 53 (New): The apparatus according to claim 52, further comprising a bias section configured to selectively apply a positive electrical potential to the conductive portion of the fixing member.

Claim 54 (New): The apparatus according to claim 53, wherein the bias section comprises a switch configured to switch between a state where the conductive portion of the fixing member is grounded and a state where the conductive portion of the fixing member is connected to the bias section.